

Method of selecting layer thicknesses of a reflective element for extreme ultra violet radiation

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- international: **G02B5/08; G21K1/06; G02B5/08; G21K1/00;** (IPC1-7):
G21K1/06; G02B5/08

- European: G02B5/08V; G02B5/08R; G21K1/06B; Y01N4/00






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Also published as:

 EP1351258 (B1)

Cited documents:

 US6295164
 EP1065568
 US5307395
 US5086443
 XP008007468
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Abstract of EP1351258

Thicknesses of molybdenum and silicon layers are selected to locate nodes of the standing electromagnetic wave field at interfaces. Alternatively they are selected to locate the antinodes before or after interfaces.

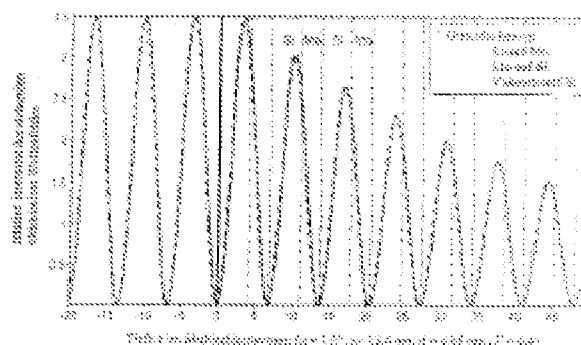


Figure 2

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